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7/22/03
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

BIN-SHING CHEN

U.S. Application No.: 09/769,576

Filing Date: January 14, 2001

For: Method for Manufacturing Split-Gate:
EEPROM Memory Cell and
Structure Formed Thereby

Group Art Unit: 2811

Examiner: Thien F. Tran

Attorney Docket No.: 3308 CON

AMENDMENT AND RESPONSE TO OFFICE ACTION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

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JUL 16 2003
TECHNOLOGY CENTER 2800

This is a response to the Office Action dated April 10, 2003, relating to the above-identified application. No fee is believed to be due in connection with this submission. However, if any fee is due, the Commissioner is authorized to charge Deposit Account No. 50-0462. Moreover, please credit any overpayment to Deposit Account No. 50-0462.

CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8

I certify that this document, along with any document referred to as being attached, is being deposited with the U.S. Postal Service as first class mail on July 10, 2003, under 37 C.F.R. §1.8 and is addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Lynne Webb
Name of person signing document

Lynne Webb
Signature of person signing document